

IN THE CLAIMS:

Claims 1-12 (Allowed)

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13. (Currently Amended) A method for reading a plurality of data from a non-volatile semiconductor memory device, said non-volatile semiconductor memory device including a memory cell storing said plurality of data, a read circuit reading said data by selecting a word line connected to said memory cell, and a data output node for outputting said data read by said read circuit, said method comprising the steps of:

reading a part of said plurality of data from said memory cell by selecting said word line;

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outputting said part of said plurality of data to said data output node;

reading another part of said plurality of data from said memory cell by selecting said word line; and

outputting said another part of said plurality of data to said data output node,

wherein

said step of outputting said part of said plurality of data overlaps with said step of reading another part of said plurality of data.

14. (Cancelled)

15. (Previously Added) A method for reading data from a non-volatile semiconductor memory device, said non-volatile semiconductor memory device including

a word line,

first and second bit lines,
a first memory cell coupled to said word line and said first bit line,
a second memory cell coupled to said word line and said second bit line, and
a data output node for outputting said data from said first and second memory cells, said method comprising the steps of:
reading first data from said first memory cell with selectively activating said word line;
outputting said first data to said data output node;
reading second data from said second memory cell with selectively activating said word line; and
outputting said second data to said data output node, wherein
said step of outputting said first data overlaps with said step of reading second data.

16. (Previously Amended) A method for writing data to a non-volatile semiconductor memory device, said non-volatile semiconductor memory device including a memory cell storing first and second data, and first and second registers, said method comprising the steps of:

storing in said first register said first data input from the outside of said non-volatile semiconductor memory device;
writing said first data stored in said first register to said memory cell;
storing in said second register said second data input from the outside of said non-volatile semiconductor memory device; and

writing said second data stored in said second register to said memory cell.

17. (Previously Added) The method according to claim 16, wherein said step of writing said first data overlaps with said step of storing said second data.

18. (Currently Amended) The method according to claim [14] 13, wherein said step of reading said another part of said plurality of data is performed after said step of reading said part of said plurality of data.

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19. (Previously Added) The method according to claim 18, wherein said step of outputting said another part of said plurality of data is performed after said step of outputting said part of said plurality of data.

20. (Previously Added) The method according to claim 15, wherein said step of reading said second data is performed after said step of reading said first data.

21. (Previously Added) The method according to claim 20, wherein said step of outputting said second data is performed after said step of outputting said first data.

22. (Previously Added) The method according to claim 17, wherein

C1 said step of storing said second data is performed after said step of storing said first data.

23. (Previously Added) The method according to claim 22, wherein said step of writing said second data is performed after said step of writing said first data.
